



Approved for use through 07/31/2003. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

Examiner  
Signature

Date  
Considered

3/18/07

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). \*See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. \*Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). \*For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. \*Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. \*Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. **DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

*If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.*



Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

Sheet 2

of

2

Attorney Docket Number	35811-00001
------------------------	-------------

**Complete if Known**

Application Number	10/720,035
--------------------	------------

Filing Date	11/21/2003
-------------	------------

First Named Inventor	Juergens, Tristan Dieter
----------------------	--------------------------

Art Unit	Unknown
----------	---------

Examiner Name	Unknown
---------------	---------

## NON PATENT LITERATURE DOCUMENTS

Examiner  
Signature

H. C. K.

Date  
Considered

3/18/07

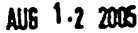
\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

60106750 1.DOC

*If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.*



Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

**(Use as many sheets as necessary)**

U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

**Examiner  
Signature**

Date  
Considered

3/18/07

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

*If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.*

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

Examiner Signature		Date Considered	3/17/09
-----------------------	---	--------------------	---------

EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.  
 Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.  
 This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.  
60126501 1.DOC



Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO

*(Use as many sheets as necessary)*

**Complete if Known**

Application Number	10/720,035
Filing Date	11/21/2003
First Named Inventor	Tsang et al.
Art Unit	3641
Examiner Name	Daniel L. Greene, Jr.
Attorney Docket Number	35811_00001

Sheet	1	of	1
-------	---	----	---

## U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

Examiner Signature		Date Considered	3/19/02
-----------------------	---	--------------------	---------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. \*Applicant's unique citation designation number (optional). \*See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. \*Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). \*For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. \*Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. \*Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.  
If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2. 60127167\_1.DOC

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

**Complete if Known**

<b>Application Number</b>	10/720,035
<b>Filing Date</b>	November 21, 2003
<b>First Named Inventor</b>	Tsang, Francis
<b>Group Art Unit</b>	3663
<b>Examiner Name</b>	Unknown

Sheet 1 of 4

Attorney Docket No: 2408.001US1

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
<i>[Handwritten]</i>	US-4,212,179	07/15/1980	Juergens, Tristan D.	10/12/1978
<i>[Handwritten]</i>	US-4,259,419	03/31/1981	Uba, Toshio, et al.	08/17/1979
<i>[Handwritten]</i>	US-4,493,221	01/15/1985	Stieg, Richard f., et al.	01/12/1983
<i>[Handwritten]</i>	US-4,521,498	06/04/1985	Juergens, Tristan	07/22/1982
<i>[Handwritten]</i>	US-4,592,972	06/03/1986	Juergens, Tristan, et al.	07/22/1983
<i>[Handwritten]</i>	US-4,606,982	08/19/1986	Nelson, Robert F., et al.	05/09/1985
<i>[Handwritten]</i>	US-5,045,086	09/03/1991	Juergens, Tristan	09/27/1989
<i>[Handwritten]</i>	US-5,047,300	09/10/1991	Juergens, Tristan	06/14/1989
<i>[Handwritten]</i>	US-5,198,313	03/30/1993	Juergens, Tristan	09/10/1991
<i>[Handwritten]</i>	US-5,677,078	10/14/1997	Juergens, Tristan, et al.	09/27/1995
<i>[Handwritten]</i>	US-5,895,728	04/20/1999	Walker, Thomas P., et al.	01/15/1997
<i>[Handwritten]</i>	US-6,004,689	12/21/1999	Walker, Thomas P., et al.	12/07/1998

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
<i>[Handwritten]</i>		"4-pocket Electron Bean Evaporator", e-flux4, tec tra, 5 Pages	
<i>[Handwritten]</i>		"Annealing (Metallurgy)", Wikipedia, <a href="http://en.wikipedia.org/wiki/Annealing_%28metallurgy%29">http://en.wikipedia.org/wiki/Annealing_%28metallurgy%29</a> , 1 Page	
<i>[Handwritten]</i>		"Carbon Coaters, Sputter Coaters and Turbo Sputter Coaters", <u>Electron Microscopy Sciences</u> , <a href="http://www.emsdiasum.com/microscopy/products/equipment/carbon_coaters.aspx">http://www.emsdiasum.com/microscopy/products/equipment/carbon_coaters.aspx</a> , 8 Pages	
<i>[Handwritten]</i>		"E-beam Evaporator", <u>Brigham Young University, Department of Electrical &amp; Computer Engineering</u> , <a href="http://www.ee.byu.edu/cleanroom/ebeam.phtml">http://www.ee.byu.edu/cleanroom/ebeam.phtml</a> , (Observed 11/7/06), 2 Pages	
<i>[Handwritten]</i>		"E-beam Evaporators", <u>Oxford Scientific</u> , <a href="http://www.oxsci.com/pages/products/evaporators/index.htm">http://www.oxsci.com/pages/products/evaporators/index.htm</a> , (Observed 11/7/06), 5 Pages	
<i>[Handwritten]</i>		"Laboratory Sputter Coating Equipment", <u>Thin Film Coating, Deposition &amp; Sputtering Equipment</u> , <a href="http://www.emitech.co.uk/sputtering-coating.htm">http://www.emitech.co.uk/sputtering-coating.htm</a> , 3 Pages	
<i>[Handwritten]</i>		"Rototherm - Thin Film Evaporator", <u>Artisan Industries, Inc.</u> , <a href="http://www.artisanind.com/chemical/rototherm.htm">http://www.artisanind.com/chemical/rototherm.htm</a> , (Observed 11/7/06), 2 Pages	
<i>[Handwritten]</i>		"Sputter Coating Technical Brief", <u>Quorum Technologies</u> , <u>Polaron</u> , Issue 1, Document No. TB-Sputter, 13 Pages	
<i>[Handwritten]</i>		"Sputter-Coater high vacuum coating system for thin film deposition", <a href="http://www.tecra.de/spuco.htm">http://www.tecra.de/spuco.htm</a> , (Observed 11/7/06), 5 Pages	
<i>[Handwritten]</i>		ALLGAIER, R. S., "Interpretation of transport Measurements in Electronically Conducting Liquids", <u>Physical Review</u> , Vol. 185, No. 1, (September 5, 1969), 227-244	

EXAMINER

DATE CONSIDERED

3/17/07

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is attached

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

**Complete if Known**

<b>Application Number</b>	10/720,035
<b>Filing Date</b>	November 21, 2003
<b>First Named Inventor</b>	Tsang, Francis
<b>Group Art Unit</b>	3663
<b>Examiner Name</b>	Unknown

Sheet 2 of 4

Attorney Docket No: 2408.001US1

**OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
<i>del</i>		BRILLSON, LEONARD J., "Contacts to Semiconductors", <u>Contacts to Semiconductors, Fundamentals and Technology</u> , Xerox Corporation, Noyes Publications, New Jersey, (1993)	
<i>del</i>		BULLOCK, ALAN, et al., "The Harper Dictionary of Modern Thought", <u>The Harper Dictionary of Modern Thought</u> , Harper & Row, New York, (1977), Page 25	
<i>del</i>		CONSIDINE, GLENN D., <u>Encyclopedia of Chemistry</u> , Fifth Edition, Van Nostrand's, John Wiley & Sons, Inc., (2005)	
<i>del</i>		CUTLER, MELVIN, "Experimental Methods", <u>Chapter 4, Liquid Semiconductors</u> , Academic Press Inc., (1977), 7 Pages	
<i>del</i>		[REDACTED]	
<i>del</i>		FARRELL, MARTIN V., et al., "Coupling of Buoyant Convections in Boron Oxide and a Molten Semiconductor in a Vertical Magnetic Field", <u>Journal of Heat Transfer</u> , Vol. 124, (August 2002), 643-649	
<i>del</i>		GEARHART, STEVEN S., et al., "A Monolithic 250 GHz Schottky-Diode Receiver", <u>IEEE Transactions on Microwave Theory and Techniques</u> , Vol. 42, No. 12, (December 1994), 2504-2511	
<i>del</i>		GHOSH, P. K., et al., "Electronic transport in Liquid and solid sulphur", <u>J. Phys. C (Proc. Phys. Soc.)</u> , Series 2, Vol. 1, (1968), 1347-1358	
<i>del</i>		GLAZOV, VASILII M., et al., "Liquid Semiconductors", <u>Liquid Semiconductors</u> , Plenum Press, New York, (1969),	
<i>del</i>		GOBRECHT, H., et al., "Electrical properties of liquid selenium up to 1300K", <u>J. Phys. C: Solid St. Phys.</u> , Vol. 4, (1971), 2247-2253	
<i>del</i>		GRAY, H. J., et al., "A New Dictionary of Physics", <u>A New Dictionary of Physics</u> , Second Edition, Longman London, (1975), Page 23	
<i>del</i>		GREACEN, CHRIS, "How Photovoltaics Cells Work", <u>Photovoltaics, Home Power # 23</u> , (June-July 1991), 37-39	
<i>del</i>		GREENWOOD, N. N., et al., "Chemistry of the Elements", <u>Chemistry of the Elements</u> , Pergamon Press, New York, (1984), Page 1121	
<i>del</i>		HARRELL, WILLIAM R., "Aluminum schottky contacts to n-type 4H-SiC", <u>Look Smart</u> , <a href="http://findarticles.com/p/articles/mi_qa3776/is_200210/ai_n9137011">http://findarticles.com/p/articles/mi_qa3776/is_200210/ai_n9137011</a> , (October 2002), 4 pages	
<i>del</i>		HARTKE, J. L., et al., "Electronic States in Vitreous Selenium", <u>Physical Review</u> , Vol. 139, No. 3A, (8/2/1965), A970-A980	
<i>del</i>		HOSOKAWA, SHINYA, et al., "Electronic Properties of Liquid Selenium Containing Alkali and Halogen Impurities", <u>Journal of the Physical Society of Japan</u> , Vol. 54, No. 12, (December 1985), 4717-4725	
<i>del</i>		IOFFE, A. F., et al., "Non-Crystalline, Amorphous, and Liquid Electronic Semiconductors", <u>Progress in Semiconductors</u> , Vol. 4, (1960), 239-291	
<i>del</i>		JAMALI, BEHNAM, et al., "Design and optimisation of Schottky diodes in CMOS technology with application to passive RFID systems", <u>School of Electrical and Electronics Engineering</u> , University of Adelaide, S.A. 5005, Australia, 9 Pages	

EXAMINER

DATE CONSIDERED

3/18/07

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 909. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant to place a check mark here if English language Translation is attached

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)


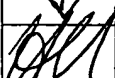
Complete if Known

Application Number	10/720,035
Filing Date	November 21, 2003
First Named Inventor	Tsang, Francis
Group Art Unit	3663
Examiner Name	Unknown

Sheet 3 of 4

Attorney Docket No: 2408.001US1

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		KNOLL, GLENN F., "Radiation Detection and Measurement", <u>Radiation Detection and Measurement</u> , Third Edition, John Wiley & Sons, Inc., New York, (2000)	
		KOSLOWSKI, THORSTEN, et al., "Modified small-world networks as models of liquid and amorphous selenium", <u>Physical Review B</u> , Vol. 66 (064205), (2002), 7 Pages	
		KRESSE, G., et al., "Defects in liquid selenium", <u>Physical Review B</u> , Vol. 59, No. 5, (1998), 3501-3513	
		LEE, CHING-TING, "Performance characterization of InGaP Schottky contact with ITO transparent electrodes", <u>Look Smart</u> , <a href="http://www.findarticles.com/p/articles/mi_qa3776/is_199809/ai_n8812313">http://www.findarticles.com/p/articles/mi_qa3776/is_199809/ai_n8812313</a> , (September 1998), 5 Pages	
		LI, QIANG, et al., "Fabrication and Modeling of Schottky Diode: Integrated in standard CMOS process", <u>State Key Lab of ASIC &amp; System</u> , Fudan University, Shang Hai 200433, 8 Pages	
		LI, MEICHENG, et al., "The Dependence of Electrical Characterization on Interface Structure of PtSi/strained-Si1-x-Ge/Si Schottky Diodes", <u>Advanced Nanomaterials and Nanodevices</u> , Eight International conference on electronic materials, China, (June 2002), 278-289	
		MERRETT, J. N., "Fabrication of self-aligned graded junction termination extensions with applications to 4H-SiC P-N diodes", <u>Look Smart</u> , <a href="http://www.findarticles.com/p/articles/mi_qa3776/is_200206/ai_n9123173">http://www.findarticles.com/p/articles/mi_qa3776/is_200206/ai_n9123173</a> , (June 2002), 5 Pages	
		MIZOBUCHI, YUZO, et al., "Photogeneration of Charge Carriers in a-sulfur", <u>Journal of the Physical Society of Japan</u> , Vol. 31, No. 1, (July 1971), 155-163	
		MONCH, W., "Semiconductor Surfaces and Interfaces", <u>Semiconductor Surfaces and Interfaces</u> , Third Edition, Springer, (2001)	
		MOTT, N. F., et al., "States in the gap and recombination in amorphous semiconductors", <u>Philosophical Magazine</u> , Vol. 32, (1975), 961-996	
		PING, A. T., "Characterization of reactive ion etching-induced damage to n-GaN surfaces using Schottky diodes", <u>Look Smart</u> , <a href="http://www.findarticles.com/p/articles/mi_qa3776/is_199703/ai_n8756708">http://www.findarticles.com/p/articles/mi_qa3776/is_199703/ai_n8756708</a> , (May 1997), 5 Pages	
		QUEHEILLALT, DOUGLAS T., et al., "Laser ultrasonic sensing of the melting and solidification of cadmium telluride", <u>Journal of Crystal Growth</u> , Vol. 225, (2001), 34-44	
		RATAKONDA, D., "Ohmic contacts formation of Silicon Schottky Diodes by Screen Printing and Rapid Isothermal Processing", <u>Look Smart</u> , <a href="http://www.findarticles.com/P/articles/mi_qa3776/is_199805/ai_n8797486">http://www.findarticles.com/P/articles/mi_qa3776/is_199805/ai_n8797486</a> , (May 1998), 3 Pages	
		REGEL, A. R., et al., "Thermal Conductivity of Salt, Metal and Semiconducting Melts", <u>Phys. stat. solidi</u> , Vol. 5., (1971), 13-57	

EXAMINER

DATE CONSIDERED

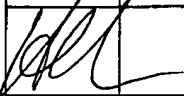
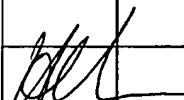
3/18/07

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) \* Applicant is to place a check mark here if English language Translation is attached



Substitute for form 1448A/PTO <b>INFORMATION DISCLOSURE          STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/720,035
	Filing Date	November 21, 2003
	First Named Inventor	Tsang, Francis
	Group Art Unit	3663
	Examiner Name	Unknown
Sheet 4 of 4	Attorney Docket No: 2408.001US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		RHINES, FREDERICK N., "Phase Diagrams in Metallurgy, Their Development and Application", <u>Phase Diagrams in Metallurgy, Their Development and Application</u> , McGraw-Hill book company, New York, (1956), Page 29	
		RHODERICK, E. H., "Metal-Semiconductor Contacts", <u>Metal-Semiconductor Contacts</u> , Second Edition, Clarendon Press, Oxford, (1988), 224-229	
		ROSSNAGEL, S. M., "Sputter deposition for semiconductor manufacturing", <u>IBM Journal of Research and Development</u> , Vol. 43, 1/2, <a href="http://www.research.ibm.com/journal/rd/431/rossnagel.html">http://www.research.ibm.com/journal/rd/431/rossnagel.html</a> , (1999), 14 Pages	
		SADOVSKII, M. V., "A model of a disordered system (A contribution to the theory of "liquid semiconductors")", <u>Sov. Phys. - JETP</u> , Vol. 39, No. 5, (November 1974), 845-850	
		SCHMITZ, A. C., "Metal contacts to n-type GaN", <u>Look Smart</u> , <a href="http://www.findarticles.com/p/articles/mi_qa3776/is_199804/ai_n8797623">http://www.findarticles.com/p/articles/mi_qa3776/is_199804/ai_n8797623</a> , (April 1998), 3 Pages	
		SZE, S. M., "Metal-Semiconductor Contacts", <u>Physics of Semiconductor Devices</u> , Second Edition, New York, John Wiley & Sons, Chapter 5, (1981), 245-311 and 820-825	
		TAI, H., et al., "Comparison of Stopping Power and Range Databases for Radiation Transport Study", <u>National Aeronautics and Space Administration, Virginia, NASA Technical Paper 3644</u> , (October 1997)	
		VAN OVERSTRAETEN, R. J., et al., "Physics, Technology and Use of Photovoltaics", <u>Physics, Technology and Use of Photovoltaics</u> , Adam Hilger Ltd, Bristol, England, (1986)	
		WANG, X. J., "Electrical characteristics of high performance Au/n-GaN Schottky diodes", <u>Look Smart</u> , <a href="http://www.findarticles.com/p/articles/mi_qa3776/is_199811/ai_n8824638">http://www.findarticles.com/p/articles/mi_qa3776/is_199811/ai_n8824638</a> , (November 1998), 5 Pages	
		WOOLLAM, JOHN A., et al., "Photoconductive and Optical Properties of Amorphous Selenium", <u>NASA Technical Note, D-6500, National Aeronautics and Space Administration, Washington D.C.</u> , (September 1971)	
		ZINGARO, RALPH A., et al., "Selenium", <u>Selenium</u> , Van Nostrand Reinhold Company, New York, (1977)	

EXAMINER

DATE CONSIDERED

3/18/07

PTO-S208A(10-01)  
Approved for use through 10/12/02 OMB 501-0001  
US Patent & Trademark Office U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it carries a valid OMB control number.

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/720,035
	Filing Date	November 21, 2003
	First Named Inventor	Tsang, Francis
	Group Art Unit	3663
	Examiner Name	Unknown
Sheet 1 of 1	Attorney Docket No: 2408.001US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
<i>[Signature]</i>		ENDERBY, J. E., "Liquid semiconductors", Rep. Prog. Phys., 53, (1990), 85-179	

EXAMINER

DATE CONSIDERED

3/18/07

Substitute Disclosure Statement Form (PTO-1449)  
 \* EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional): Applicant is to place a check mark here if English language Translation is attached.